

NPN SILICON RF MICROWAVE TRANSISTOR

DESCRIPTION:

The **ASI MSC80917** is low level Class-C, Common Base Device Designed for IFF, DME driver Applications.

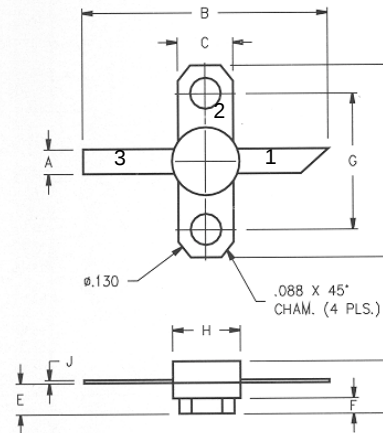
FEATURES INCLUDE:

- **Omnigold™** Metalization System
- P_{OUT} 4.0 W Min.
- $G_P = 10$ dB

MAXIMUM RATINGS

I_C	1.0 A
V_{CE}	37 V
P_{DISS}	7.5 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
θ_{JC}	$35^\circ C/W$

PACKAGE STYLE .280 2L FL (B)



	MINIMUM INCHES/MM	MAXIMUM INCHES/MM		MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	.100/2,54		J	.003/0,08	.006/0,15
B	1.050/26,67				
C	.250/6,35				
D		.210/5,33			
E	.120/3,05	.130/3,30			
F	.062/1,58				
G	.562/14,28				
H		.285/7,24			
I	.800/20,32				

1 = COLLECTOR

2 = BASE

3 = EMITTER

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 1.0$ mA	45			V
BV_{CEO}	$I_C = 5.0$ mA	20			V
BV_{EBO}	$I_E = 1.0$ mA	3.5			V
I_{CES}	$V_{CE} = 35$ V			1.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 100$ mA	20		120	
G_P	$V_{CE} = 35$ V $P_{IN} = 400$ mW $f = 1025$ to 1150 MHz	10			dB
P_{OUT}	PULSE WIDTH = 10 μ S DUTY CYCLE = 1.0%	4.0			W
η		35			%